



<IGBT Modules>

CM75MXUB-13T/CM75MXUBP-13T

**HIGH POWER SWITCHING USE
INSULATED TYPE**

 <p>MXUB</p>	<p>Collector current I_c 75 A Collector-emitter voltage V_{CES} 650 V Maximum junction temperature T_{vjmax} 175 °C</p> <ul style="list-style-type: none"> •Flat base type •Copper base plate (Nickel-plating) •RoHS Directive compliant •Tin-plating pin terminals
 <p>MXUBP</p>	<p>Collector current I_c 75 A Collector-emitter voltage V_{CES} 650 V Maximum junction temperature T_{vjmax} 175 °C</p> <ul style="list-style-type: none"> •Flat base type •Copper base plate (Nickel-plating) •RoHS Directive compliant •Tin-plating pressfit terminals <p>•UL Recognized under UL1557, File No. E323585</p>

CIB (Converter+Inverter+Chopper Brake)

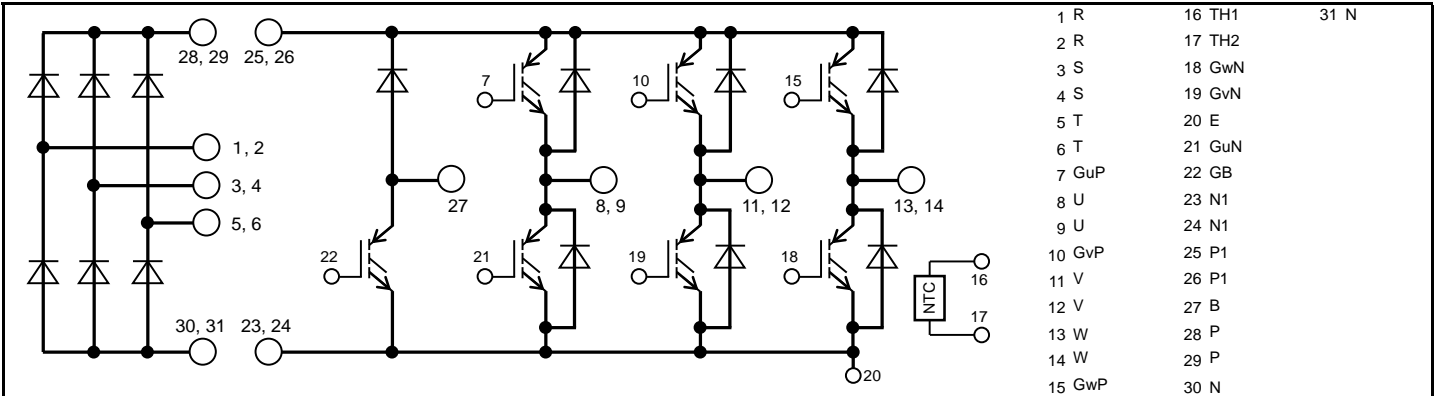
APPLICATION

AC Motor Control, Motion/Servo Control, Power supply, etc.

OPTION (Below options are available.)

- PC-TIM (Phase Change Thermal Interface Material) pre-apply

INTERNAL CONNECTION

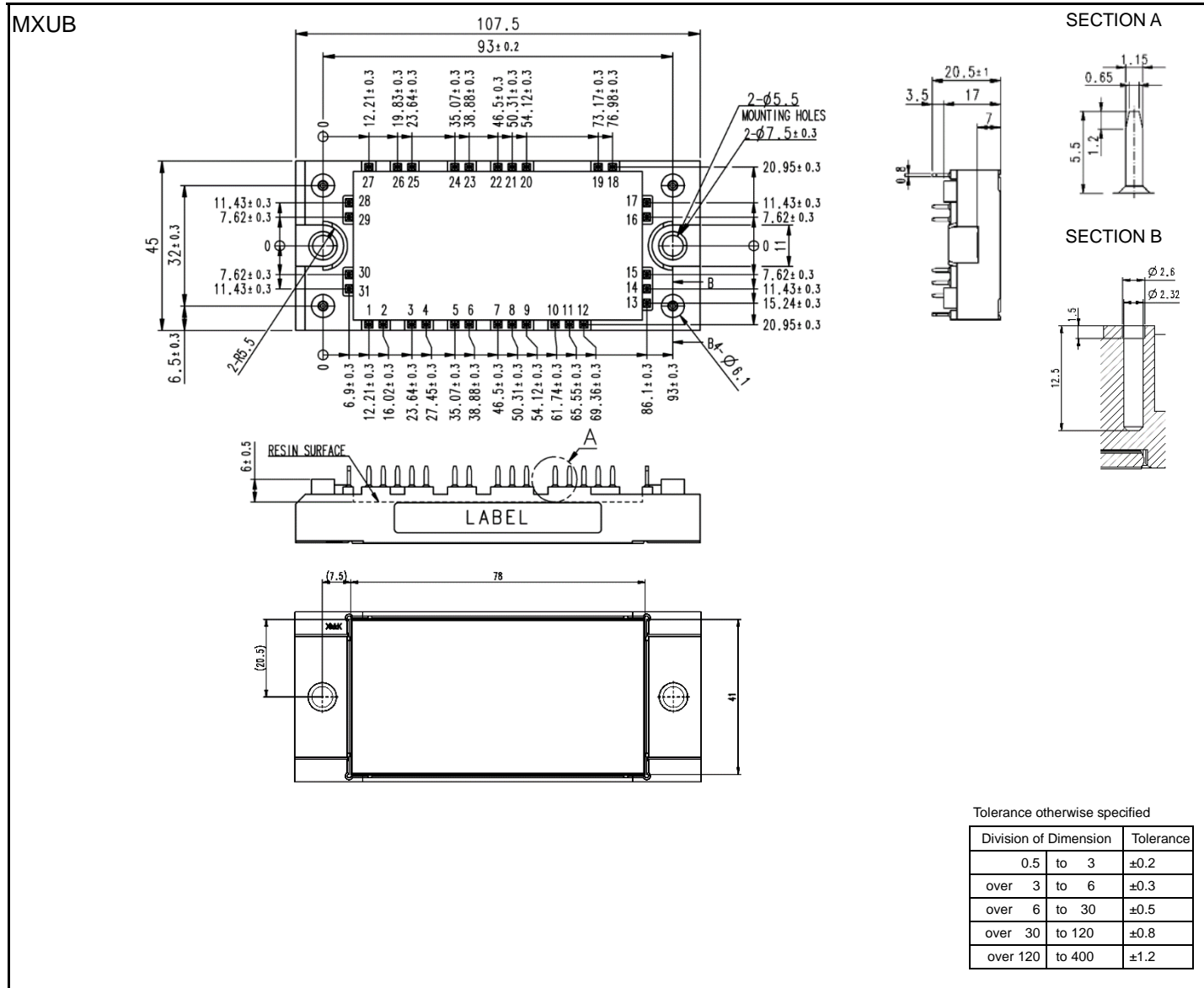


CM75MXUB-13T/CM75MXUBP-13T

HIGH POWER SWITCHING USE
INSULATED TYPE

OUTLINE DRAWING

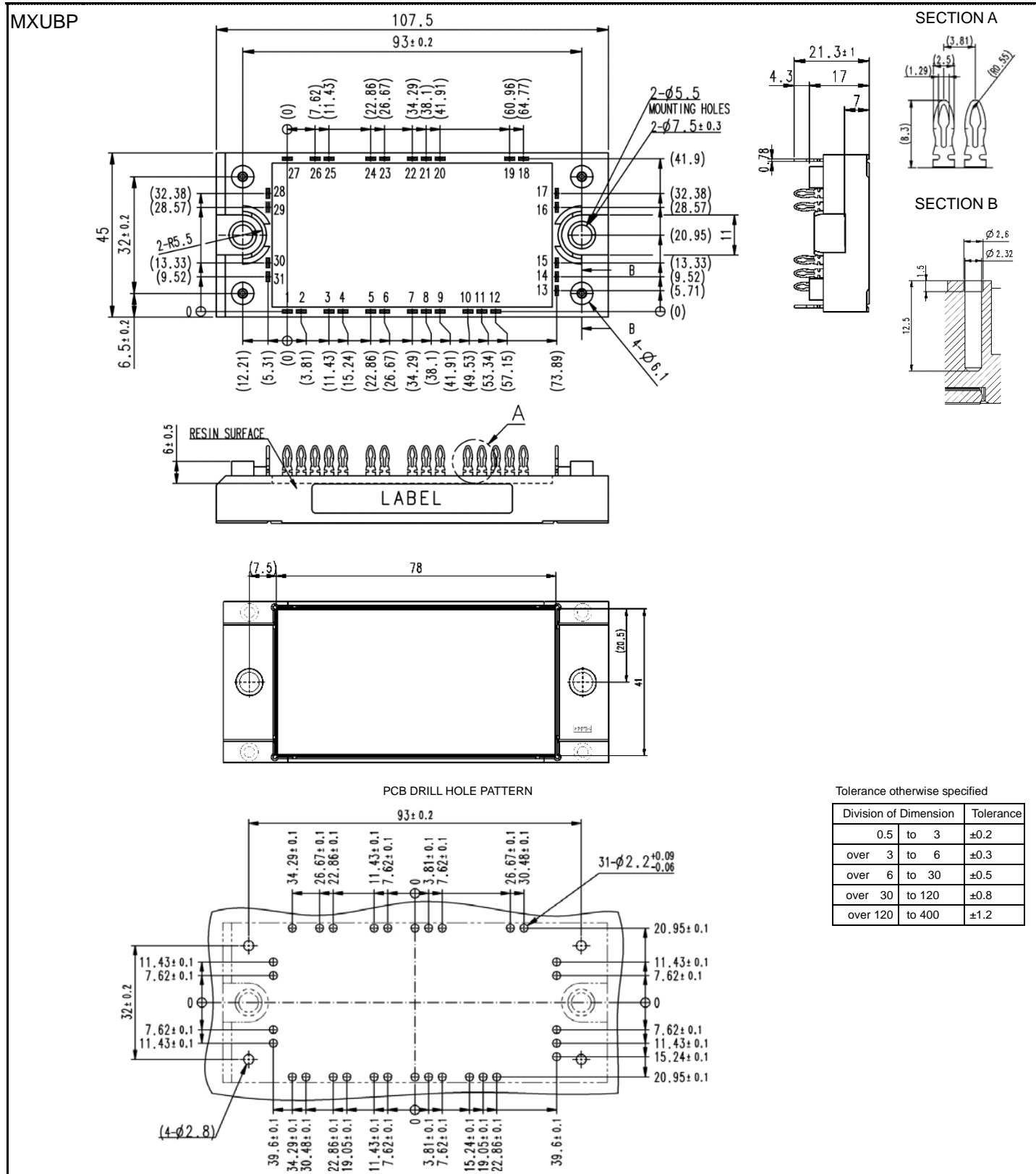
Dimension in mm



CM75MXUB-13T/CM75MXUBP-13T

HIGH POWER SWITCHING USE
INSULATED TYPE

OUTLINE DRAWING



CM75MXUB-13T/CM75MXUBP-13THIGH POWER SWITCHING USE
INSULATED TYPE**MAXIMUM RATINGS (T_{vj}=25 °C, unless otherwise specified)****INVERTER PART IGBT/FWD**

Symbol	Item	Conditions	Rating	Unit
V _{CES}	Collector-emitter voltage	G-E short-circuited	650	V
V _{GES}	Gate-emitter voltage	C-E short-circuited	± 20	V
I _C	Collector current	DC, T _C =114°C (Note2, 4)	75	A
I _{CRM}		Pulse, Repetitive (Note3)	150	
P _{tot}	Total power dissipation	T _C =25 °C (Note2, 4)	325	W
I _E (Note1)	Emitter current	DC (Note2)	75	A
I _{ERM} (Note1)		Pulse, Repetitive (Note3)	150	
T _{vjmax}	Maximum junction temperature	Instantaneous event (overload)	175	°C

BRAKE PART IGBT/DIODE

Symbol	Item	Conditions	Rating	Unit
V _{CES}	Collector-emitter voltage	G-E short-circuited	650	V
V _{GES}	Gate-emitter voltage	C-E short-circuited	± 20	V
I _C	Collector current	DC, T _C =125 °C (Note2, 4)	50	A
I _{CRM}		Pulse, Repetitive (Note3)	100	
P _{tot}	Total power dissipation	T _C =25 °C (Note2, 4)	270	W
V _{RRM}	Repetitive peak reverse voltage	G-E short-circuited	650	V
I _F	Forward current	DC (Note2)	35	A
I _{FRM}		Pulse, Repetitive (Note3)	70	
T _{vjmax}	Maximum junction temperature	Instantaneous event (overload)	175	°C

CONVERTER PART DIODE

Symbol	Item	Conditions	Rating	Unit	
V _{RRM}	Repetitive peak reverse voltage	-	800	V	
E _a	Recommended AC input voltage	RMS	220	V	
I _o	DC output current	3-phase full wave rectifying, T _C =125 °C (Note4)	75	A	
I _{FSM}	Surge forward current	The sine half wave 1 cycle peak value, f=60 Hz, non-repetitive	T _{vj} =25 °C	900	A
			T _{vj} =150 °C	720	
I ² _t	Current square time	Value for one cycle of surge current	T _{vj} =25 °C	3375	A ² s
			T _{vj} =150 °C	2160	
T _{vjmax}	Maximum junction temperature	Instantaneous event (overload)	150	°C	

MODULE

Symbol	Item	Conditions	Rating	Unit
V _{isol}	Isolation voltage	Terminals to base plate, RMS, f=60 Hz, AC 1 min	2500	V
T _{Cmax}	Maximum case temperature	(Note4)	125	°C
T _{vjop}	Operating junction temperature	Continuous operation (under switching)	-40 ~ +150	°C
T _{stg}	Storage temperature	-	-40 ~ +125	

CM75MXUB-13T/CM75MXUBP-13T

HIGH POWER SWITCHING USE
INSULATED TYPE**ELECTRICAL CHARACTERISTICS (T_{vj}=25 °C, unless otherwise specified)**
INVERTER PART IGBT/FWD

Symbol	Item	Conditions	Limits			Unit	
			Min.	Typ.	Max.		
I _{CES}	Collector-emitter cut-off current	V _{CE} =V _{CES} , G-E short-circuited	-	-	1.0	mA	
I _{GES}	Gate-emitter leakage current	V _{GE} =V _{GES} , C-E short-circuited	-	-	0.5	μA	
V _{GE(th)}	Gate-emitter threshold voltage	I _C =7.5 mA, V _{CE} =10 V	5.4	6.0	6.6	V	
V _{CEsat} (Terminal)	Collector-emitter saturation voltage	I _C =75 A, V _{GE} =15 V, Refer to the figure of test circuit (Note5)	T _{vj} =25 °C	-	1.45	1.90	V
			T _{vj} =125 °C	-	1.60	-	
			T _{vj} =150 °C	-	1.65	-	
V _{CEsat} (Chip)	Collector-emitter saturation voltage	I _C =75 A, V _{GE} =15 V, (Note5)	T _{vj} =25 °C	-	1.30	1.55	V
			T _{vj} =125 °C	-	1.35	-	
			T _{vj} =150 °C	-	1.35	-	
C _{ies}	Input capacitance	V _{CE} =10 V, G-E short-circuited	-	-	10.1	nF	
C _{oes}	Output capacitance		-	-	0.5		
C _{res}	Reverse transfer capacitance		-	-	0.2		
Q _G	Gate charge	V _{CC} =300 V, I _C =75 A, V _{GE} =15 V	-	0.31	-	μC	
t _{d(on)}	Turn-on delay time	V _{CC} =300 V, I _C =75 A, V _{GE} =±15 V, R _G =8.2 Ω, Inductive load	-	-	400	ns	
t _r	Rise time		-	-	200		
t _{d(off)}	Turn-off delay time		-	-	400		
t _f	Fall time		-	-	600		
V _{EC} (Note1) (Terminal)	Emitter-collector voltage	I _E =75 A, G-E short-circuited, Refer to the figure of test circuit (Note5)	T _{vj} =25 °C	-	1.60	2.05	V
			T _{vj} =125 °C	-	1.70	-	
			T _{vj} =150 °C	-	1.75	-	
V _{EC} (Note1) (Chip)	Emitter-collector voltage	I _E =75 A, G-E short-circuited, (Note5)	T _{vj} =25 °C	-	1.40	1.80	V
			T _{vj} =125 °C	-	1.40	-	
			T _{vj} =150 °C	-	1.40	-	
t _{rr} (Note1)	Reverse recovery time	V _{CC} =300 V, I _E =75 A, V _{GE} =±15 V,	-	-	400	ns	
Q _{rr} (Note1)	Reverse recovery charge	R _G =8.2 Ω, Inductive load	-	6.0	-	μC	
E _{on}	Turn-on switching energy per pulse	V _{CC} =300 V, I _C =I _E =75 A,	-	2.1	-	mJ	
E _{off}	Turn-off switching energy per pulse	V _{GE} =±15 V, R _G =8.2Ω, T _{vj} =150 °C,	-	4.0	-		
E _{rr} (Note1)	Reverse recovery energy per pulse	Inductive load	-	4.5	-	mJ	
r _g	Internal gate resistance	Per switch	-	0	-	Ω	

BRAKE PART IGBT/DIODE

Symbol	Item	Conditions	Limits			Unit	
			Min.	Typ.	Max.		
I _{CES}	Collector-emitter cut-off current	V _{CE} =V _{CES} , G-E short-circuited	-	-	1.0	mA	
I _{GES}	Gate-emitter leakage current	V _{GE} =V _{GES} , C-E short-circuited	-	-	0.5	μA	
V _{GE(th)}	Gate-emitter threshold voltage	I _C =5.0 mA, V _{CE} =10 V	5.4	6.0	6.6	V	
V _{CEsat} (Terminal)	Collector-emitter saturation voltage	I _C =50 A, V _{GE} =15 V, Refer to the figure of test circuit (Note5)	T _{vj} =25 °C	-	1.40	1.85	V
			T _{vj} =125 °C	-	1.55	-	
			T _{vj} =150 °C	-	1.60	-	
V _{CEsat} (Chip)	Collector-emitter saturation voltage	I _C =50 A, V _{GE} =15 V, (Note5)	T _{vj} =25 °C	-	1.30	1.55	V
			T _{vj} =125 °C	-	1.35	-	
			T _{vj} =150 °C	-	1.35	-	
C _{ies}	Input capacitance	V _{CE} =10 V, G-E short-circuited	-	-	6.7	nF	
C _{oes}	Output capacitance		-	-	0.3		
C _{res}	Reverse transfer capacitance		-	-	0.1		
Q _G	Gate charge	V _{CC} =300 V, I _C =50 A, V _{GE} =15 V	-	0.21	-	μC	
t _{d(on)}	Turn-on delay time	V _{CC} =300 V, I _C =50 A, V _{GE} =±15 V, R _G =12 Ω, Inductive load	-	-	400	ns	
t _r	Rise time		-	-	200		
t _{d(off)}	Turn-off delay time		-	-	400		
t _f	Fall time		-	-	600		

CM75MXUB-13T/CM75MXUBP-13T

HIGH POWER SWITCHING USE
INSULATED TYPE

ELECTRICAL CHARACTERISTICS (cont.; $T_{vj}=25\text{ }^{\circ}\text{C}$, unless otherwise specified)

BRAKE PART IGBT/DIODE

Symbol	Item	Conditions	Limits			Unit		
			Min.	Typ.	Max.			
E_{on}	Turn-on switching energy per pulse	$V_{CC}=300\text{ V}$, $V_{GE}=\pm 15\text{ V}$, $T_{vj}=150\text{ }^{\circ}\text{C}$, Inductive load	$I_C=50\text{ A}$, $R_G=12\text{ }\Omega$	-	0.9	-	mJ	
E_{off}	Turn-off switching energy per pulse			-	2.3	-		
E_{rr}	Reverse recovery energy per pulse			$I_E=50\text{ A}$, $R_G=12\text{ }\Omega$	-	2.2		-
r_g	Internal gate resistance	-	-	0	-	Ω		
I_{RRM}	Reverse current	$V_R=V_{RRM}$, G-E short-circuited	-	-	1.0	mA		
V_F (Terminal)	Forward voltage	$I_F=35\text{ A}$, G-E short-circuited, Refer to the figure of test circuit (Note5)		$T_{vj}=25\text{ }^{\circ}\text{C}$	-	1.55	2.10	V
				$T_{vj}=125\text{ }^{\circ}\text{C}$	-	1.65	-	
				$T_{vj}=150\text{ }^{\circ}\text{C}$	-	1.70	-	
V_F (Chip)	Forward voltage	$I_F=35\text{ A}$, G-E short-circuited, (Note5)		$T_{vj}=25\text{ }^{\circ}\text{C}$	-	1.45	1.85	V
				$T_{vj}=125\text{ }^{\circ}\text{C}$	-	1.50	-	
				$T_{vj}=150\text{ }^{\circ}\text{C}$	-	1.50	-	
t_{rr}	Reverse recovery time	$V_{CC}=300\text{ V}$, $I_F=35\text{ A}$, $V_{GE}=\pm 15\text{ V}$,	-	-	400	ns		
Q_{rr}	Reverse recovery charge	$R_G=18\text{ }\Omega$, Inductive load	-	4.0	-	μC		

CONVERTER PART DIODE

Symbol	Item	Conditions	Limits			Unit		
			Min.	Typ.	Max.			
I_{RRM}	Repetitive peak reverse current	$V_R=V_{RRM}$, $T_{vj}=150\text{ }^{\circ}\text{C}$	-	-	20	mA		
V_F (Terminal)	Forward voltage	$I_F=75\text{ A}$		$T_{vj}=25\text{ }^{\circ}\text{C}$	-	1.25	1.70	V
				$T_{vj}=150\text{ }^{\circ}\text{C}$	-	1.20	-	
V_F (chip)				$T_{vj}=25\text{ }^{\circ}\text{C}$	-	1.15	1.40	
				$T_{vj}=150\text{ }^{\circ}\text{C}$	-	1.10	-	

NTC THERMISTOR PART

Symbol	Item	Conditions	Limits			Unit
			Min.	Typ.	Max.	
R_{25}	Zero-power resistance	$T_C=25\text{ }^{\circ}\text{C}$ (Note4)	4.85	5.00	5.15	k Ω
$\Delta R/R$	Deviation of resistance	$R_{100}=493\text{ }\Omega$, $T_C=100\text{ }^{\circ}\text{C}$ (Note4)	-7.3	-	+7.8	%
$B_{(25/50)}$	B-constant	Approximate by equation (Note6)	-	3375	-	K
P_{25}	Power dissipation	$T_C=25\text{ }^{\circ}\text{C}$ (Note4)	-	-	10	mW

THERMAL RESISTANCE CHARACTERISTICS

Symbol	Item	Conditions	Limits			Unit	
			Min.	Typ.	Max.		
$R_{th(j-c)Q}$	Thermal resistance	Junction to case, per Inverter IGBT (Note4)	-	-	458	K/kW	
$R_{th(j-c)D}$		Junction to case, per Inverter FWD (Note4)	-	-	594		
$R_{th(j-c)Q}$		Junction to case, Brake IGBT (Note4)	-	-	554		
$R_{th(j-c)D}$		Junction to case, Brake DIODE (Note4)	-	-	1346		
$R_{th(j-c)D}$		Junction to case, per Converter DIODE (Note4)	-	-	650		
$R_{th(c-s)}$	Contact thermal resistance	Case to heat sink, per 1 module,	Thermal grease applied (Note4, 7)	-	20.2	-	K/kW
			PC-TIM applied (Note4, 8)	-	5.5	-	

CM75MXUB-13T/CM75MXUBP-13T

HIGH POWER SWITCHING USE
INSULATED TYPE

MECHANICAL CHARACTERISTICS

Symbol	Item	Conditions	Limits			Unit	
			Min.	Typ.	Max.		
M _s	Mounting torque	Mounting to heat sink M 5 screw	2.5	3.0	3.5	N·m	
d _s	Creepage distance	Solder pin type(MXUB)	Terminal to terminal	10.9	-	-	mm
			Terminal to base plate	18.3	-	-	
		Pressfit pin type(MXUBP)	Terminal to terminal	5.2	-	-	
			Terminal to base plate	16.1	-	-	
d _a	Clearance	Solder pin type(MXUB)	Terminal to terminal	6.5	-	-	mm
			Terminal to base plate	13.1	-	-	
		Pressfit pin type(MXUBP)	Terminal to terminal	5.0	-	-	
			Terminal to base plate	16.1	-	-	
e _c	Flatness of base plate	On the centerline X, Y (Note9)	±0	-	+200	µm	
m	mass	-	-	165	-	g	

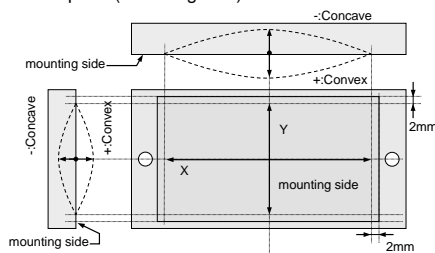
RECOMMENDED OPERATING CONDITIONS

Symbol	Item	Conditions	Limits			Unit
			Min.	Typ.	Max.	
V _{CC}	(DC) Supply voltage	Applied across P-N(P1-N1) terminals	-	300	450	V
V _{GEon}	Gate (-emitter drive) voltage	Applied across G*P-*/G*N-E/GB-E terminals (*=U,V,W)	13.5	15.0	16.5	V
R _G	External gate resistance	Inverter IGBT, Per switch	8.2	-	82	Ω
		Brake IGBT	12	-	120	

*: This product is compliant with the Restriction of the Use of Certain Hazardous Substances in Electrical and Electronic Equipment (RoHS) directive 2011/65/EU.

Note1. Represent ratings and characteristics of the anti-parallel, emitter-collector free-wheeling diode (FWD).

- Junction temperature (T_{vj}) should not increase beyond T_{vjmax} rating.
- Pulse width and repetition rate should be such that the device junction temperature (T_{vj}) dose not exceed T_{vjmax} rating.
- Case temperature (T_c) and heat sink temperature (T_s) are defined on the each surface (mounting side) of base plate and heat sink just under the chips.
Refer to the figure of chip location.
- Pulse width and repetition rate should be such as to cause negligible temperature rise. Refer to the figure of test circuit.
- $B_{(25/50)} = \ln\left(\frac{R_{25}}{R_{50}}\right) / \left(\frac{1}{T_{25}} - \frac{1}{T_{50}}\right)$
R₂₅: resistance at absolute temperature T₂₅ [K]; T₂₅=25 [°C]+273.15=298.15 [K]
R₅₀: resistance at absolute temperature T₅₀ [K]; T₅₀=50 [°C]+273.15=323.15 [K]
- Typical value is measured by using thermally conductive grease of λ=0.9 W/(m·K)/D_(c-s)=50 µm.
- Typical value is measured by using PC-TIM of λ=3.4 W/(m·K)/D_(c-s)=50 µm.
- The base plate (mounting side) flatness measurement points (X, Y) are shown in the following figure.



- Use the following screws when mounting the printed circuit board (PCB) on the standoffs.

PCB thickness : t1.6

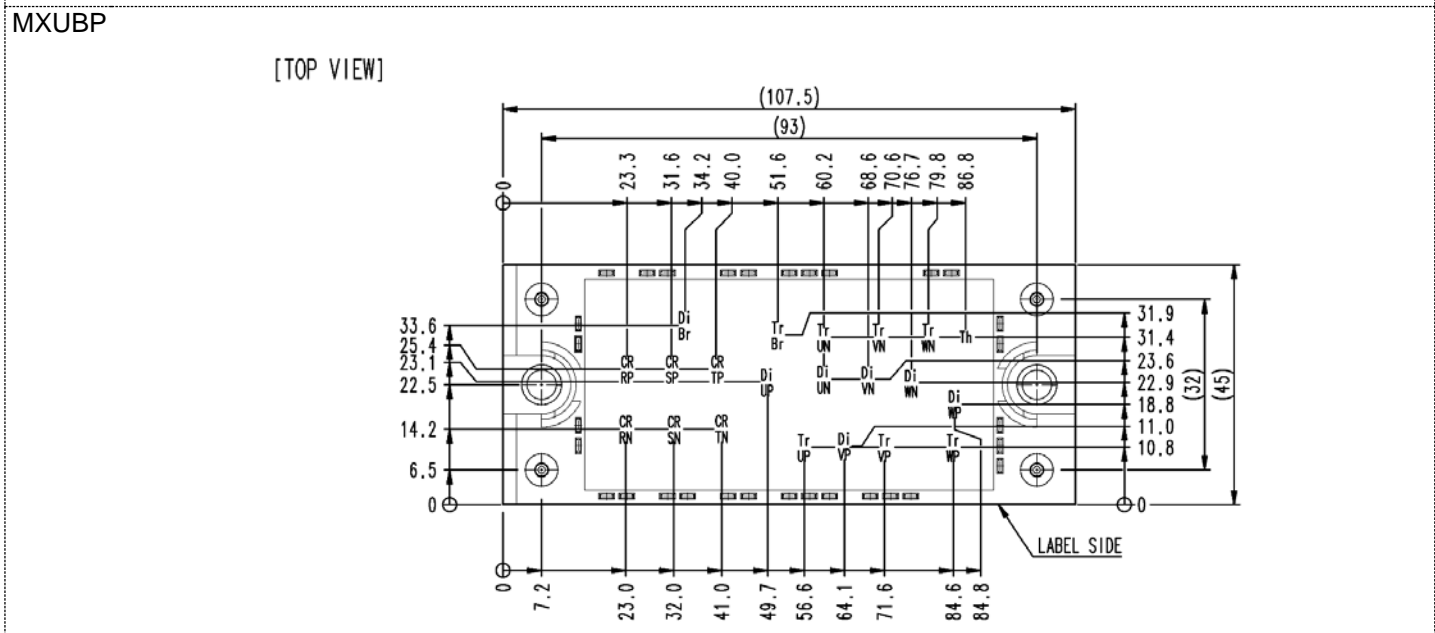
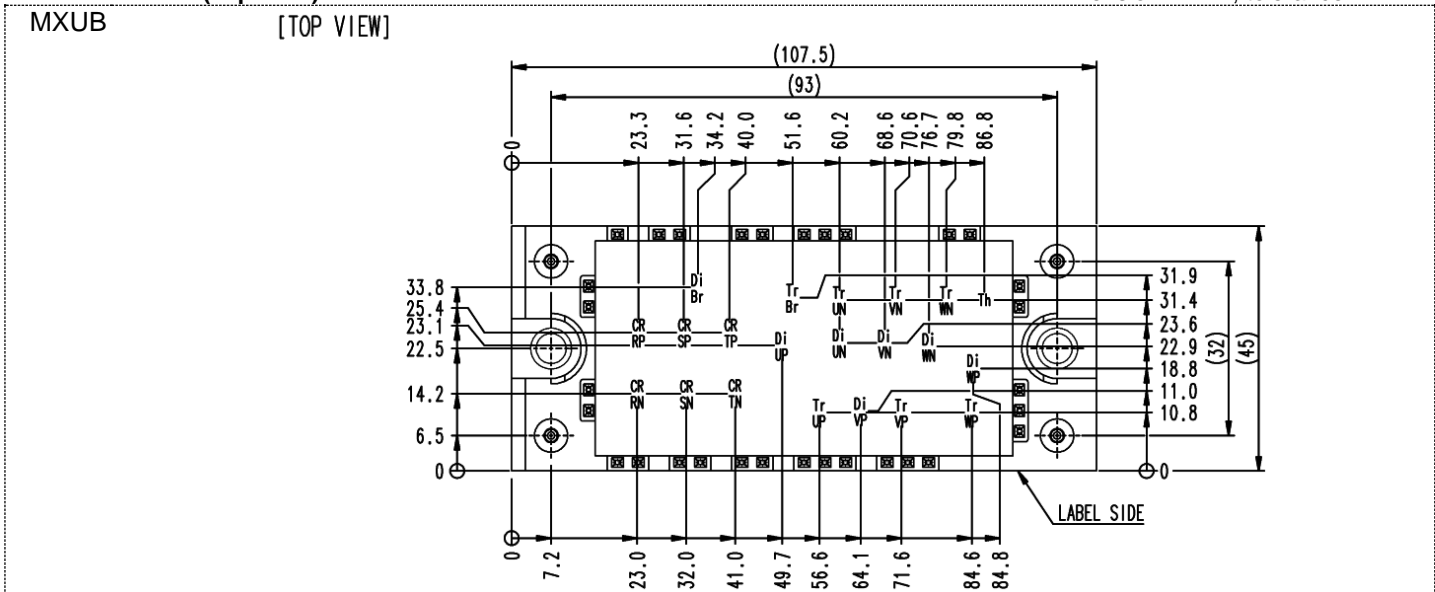
Type	Manufacturer	Size	Tightening torque (N·m)	Recommended tightening method
(1) PT®	EJOT	K25×8	0.55 ± 0.055	by handwork (equivalent to 30 rpm by mechanical screw driver) ~ 600 rpm (by mechanical screw driver)
(2) PT®		K25×10	0.75 ± 0.075 N·m	
(3) DELTA PT®		25×8	0.55 ± 0.055 N·m	
(4) DELTA PT®		25×10	0.75 ± 0.075 N·m	
(5) B1 tapping screw	-	φ2.6×10 φ2.6×12	0.75 ± 0.075 N·m	

CM75MXUB-13T/CM75MXUBP-13T

HIGH POWER SWITCHING USE
INSULATED TYPE

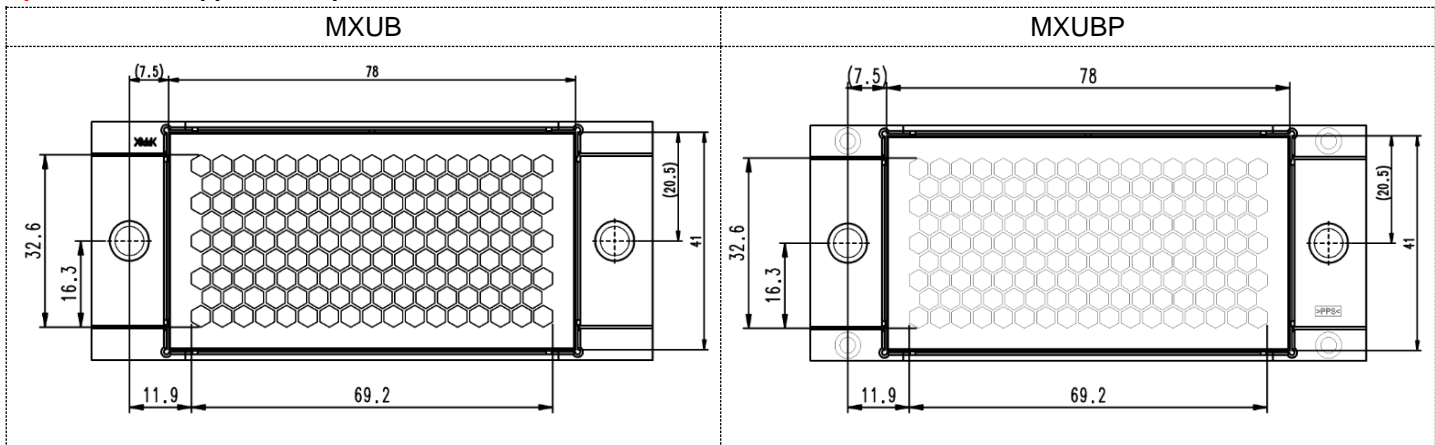
CHIP LOCATION (Top view)

Dimension in mm, tolerance: ±1 mm



Tr*P/Tr*N/TrBr: IGBT, Di*P/Di*N: DIODE (*=U/V/W), DiBr: BRAKE DIODE,
CR*P/CR*N: CONVERTER DIODE (*=R/S/T), Th: NTC thermistor

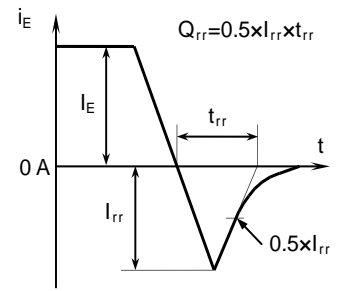
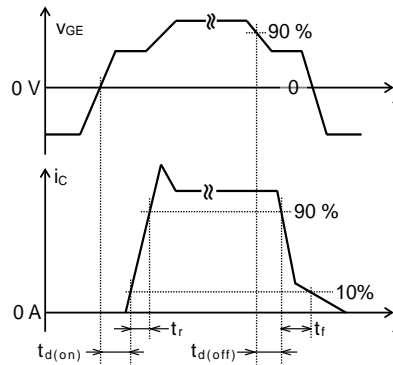
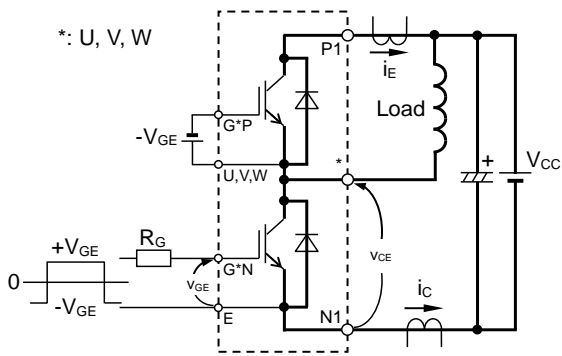
Option: PC-TIM applied baseplate outline



CM75MXUB-13T/CM75MXUBP-13T

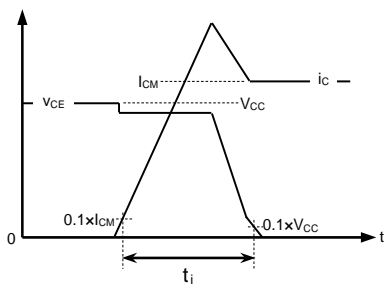
HIGH POWER SWITCHING USE
INSULATED TYPE

TEST CIRCUIT AND WAVEFORMS

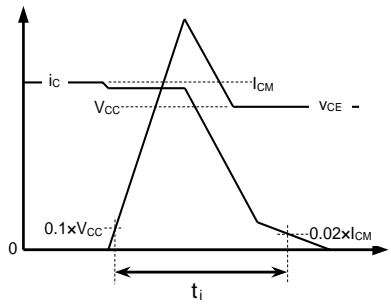


Switching characteristics test circuit and waveforms

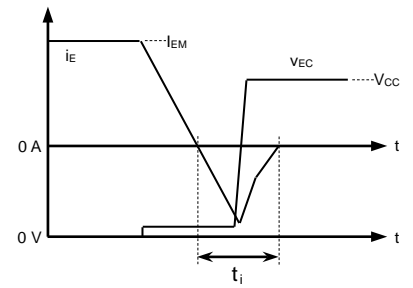
t_{rr} , Q_{rr} characteristics test waveform



IGBT Turn-on switching energy



IGBT Turn-off switching energy



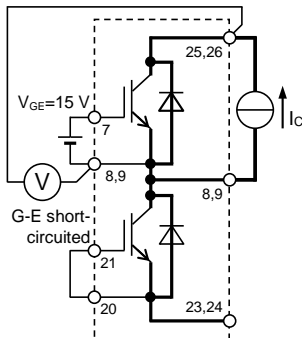
FWD Reverse recovery energy

Switching energy and Reverse recovery energy test waveforms (Integral time instruction drawing)

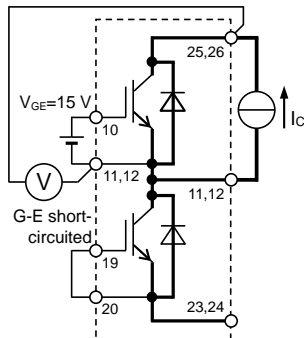
CM75MXUB-13T/CM75MXUBP-13T

HIGH POWER SWITCHING USE
INSULATED TYPE

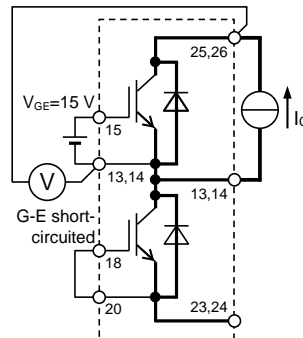
TEST CIRCUIT



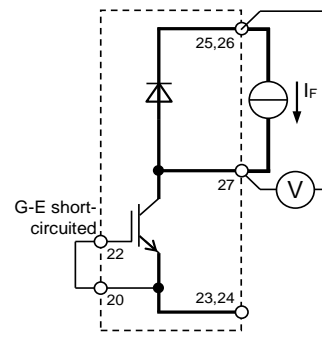
TrUP



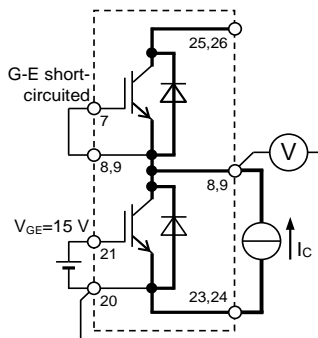
TrVP



TrWP

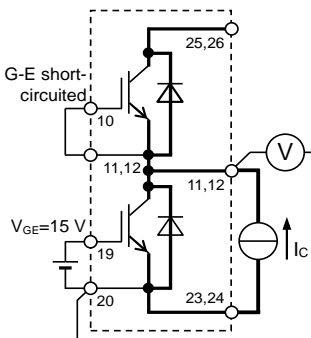


Brake DIODE



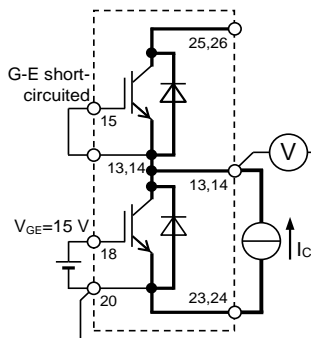
TrUN

Gate-emitter GVP-V, GVN-E,
short-circuited GWP-W, GWN-E
GB-E



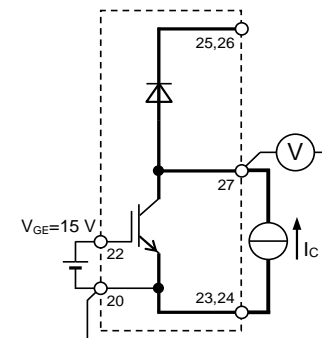
TrVN

Gate-emitter GUP-U, GUN-E,
short-circuited GWP-W, GWN-E
GB-E



TrWN

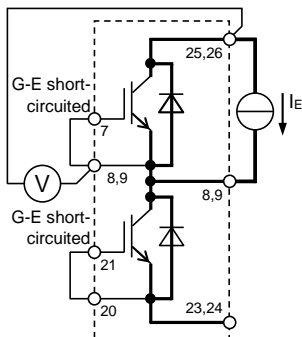
Gate-emitter GUP-U, GUN-E,
short-circuited GVP-V, GVN-E
GB-E



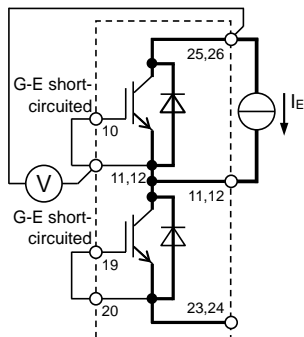
Brake IGBT

Gate-emitter GUP-U, GUN-E,
short-circuited GVP-V, GVN-E,
GWP-W, GWN-E

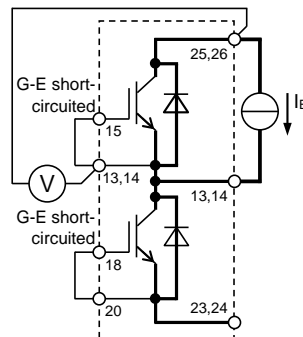
V_{CEsat} /BRAKE DIODE V_F characteristics test circuit



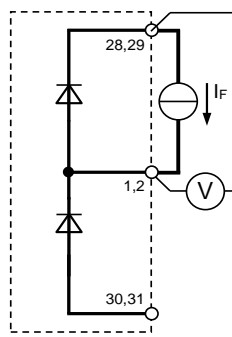
DiUP



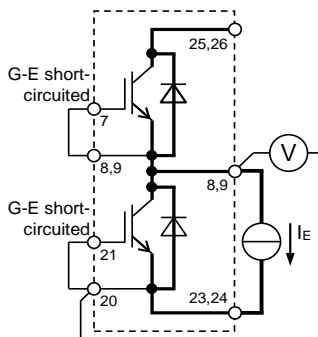
DiVP



DiWP

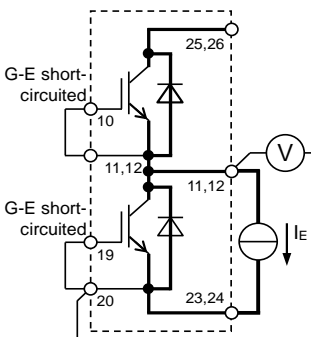


CONVERTER DIODE (ex.phase-R)



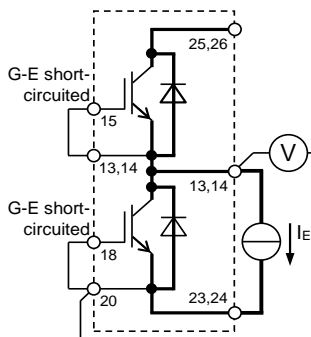
DiUN

Gate-emitter GVP-V, GVN-E,
short-circuited GWP-W, GWN-E
GB-E



DiVN

Gate-emitter GUP-U, GUN-E,
short-circuited GWP-W, GWN-E
GB-E



DiWN

Gate-emitter GUP-U, GUN-E,
short-circuited GVP-V, GVN-E
GB-E

V_{EC} / CONVERTER DIODE V_F characteristics test circuit

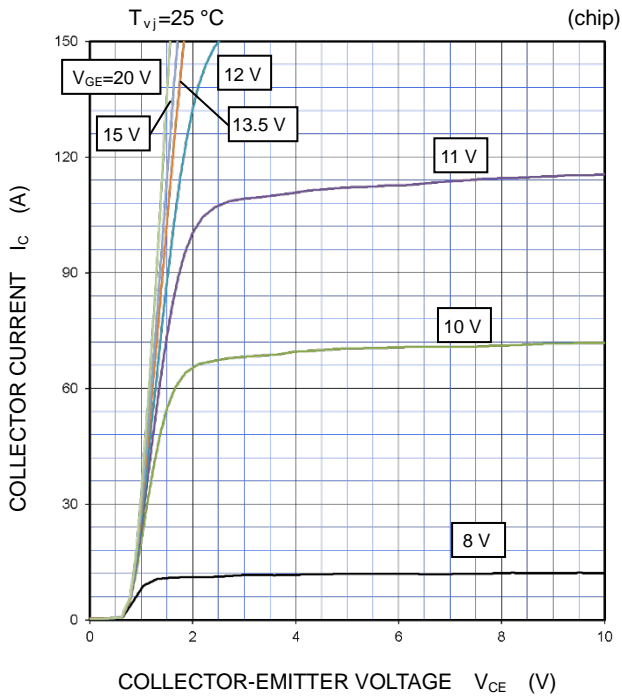
CM75MXUB-13T/CM75MXUBP-13T

HIGH POWER SWITCHING USE
INSULATED TYPE

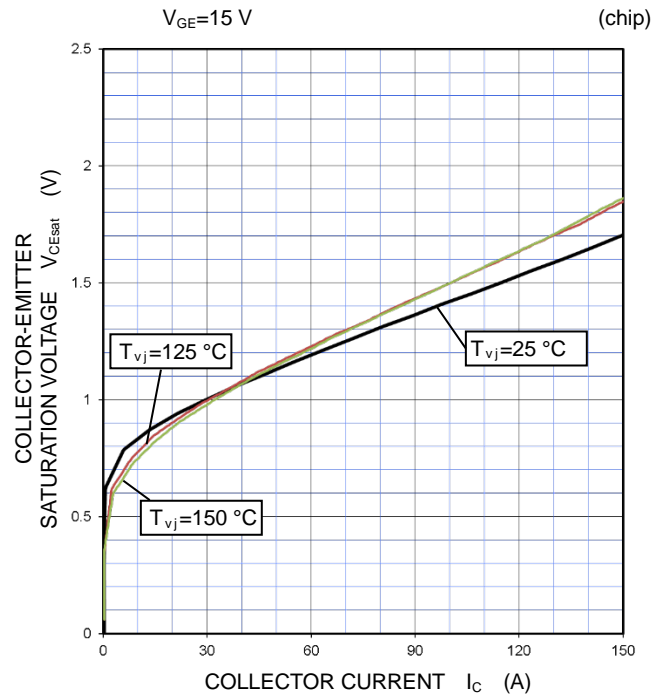
PERFORMANCE CURVES

INVERTER PART

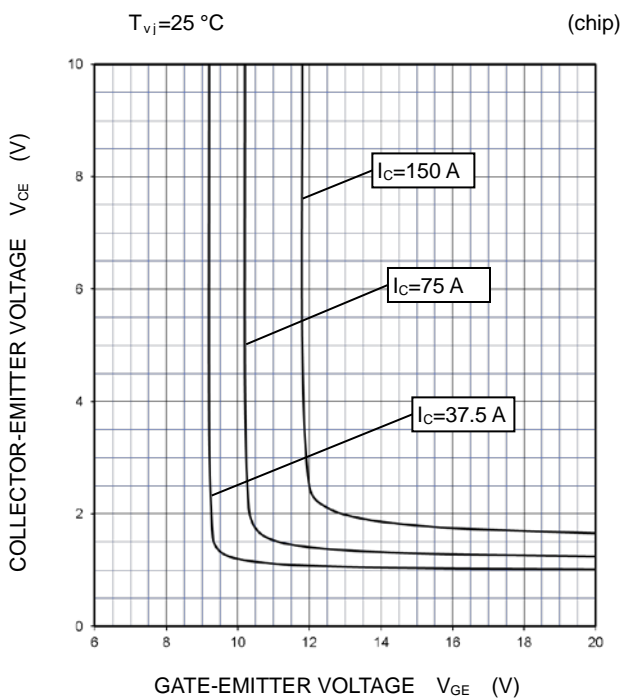
OUTPUT CHARACTERISTICS
(TYPICAL)



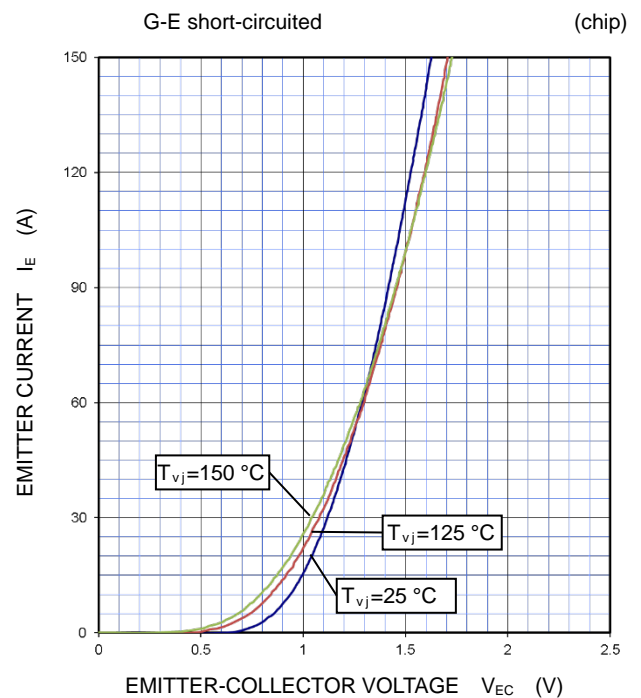
COLLECTOR-EMITTER SATURATION VOLTAGE
CHARACTERISTICS
(TYPICAL)



COLLECTOR-EMITTER VOLTAGE CHARACTERISTICS
(TYPICAL)



FREE WHEELING DIODE
FORWARD CHARACTERISTICS
(TYPICAL)



CM75MXUB-13T/CM75MXUBP-13T

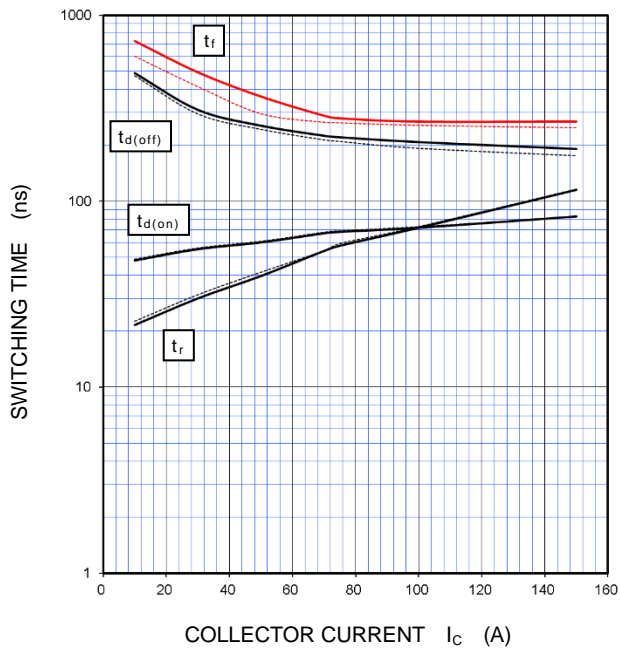
HIGH POWER SWITCHING USE
INSULATED TYPE

PERFORMANCE CURVES

INVERTER PART

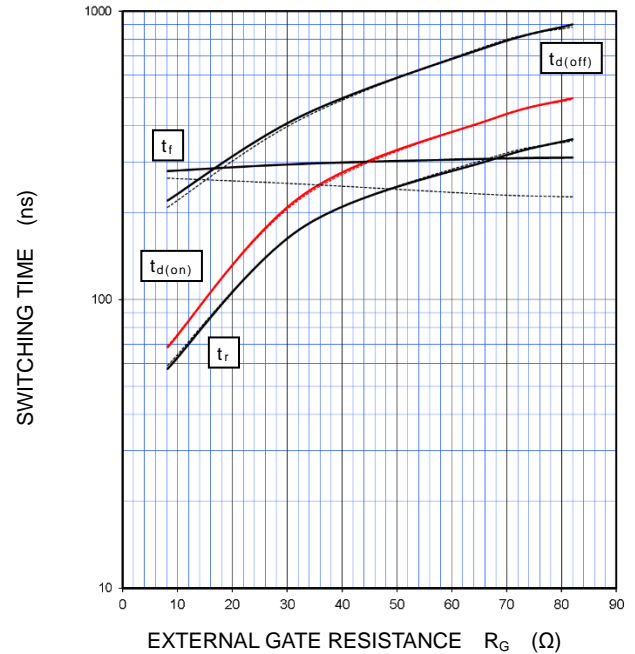
HALF-BRIDGE SWITCHING CHARACTERISTICS (TYPICAL)

$V_{CC}=300\text{ V}$, $R_G=8.2\ \Omega$, $V_{GE}=\pm 15\text{ V}$, INDUCTIVE LOAD
 —: $T_{vj}=150\text{ }^\circ\text{C}$, - - - -: $T_{vj}=125\text{ }^\circ\text{C}$



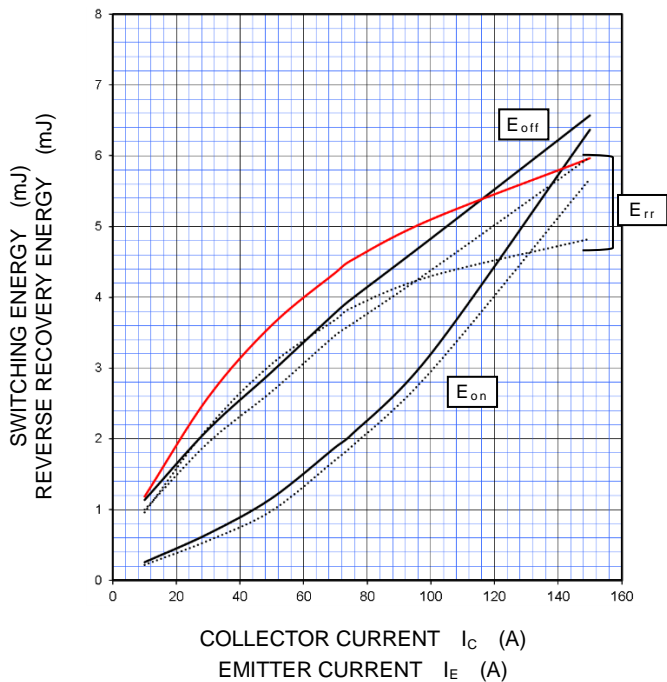
HALF-BRIDGE SWITCHING CHARACTERISTICS (TYPICAL)

$V_{CC}=300\text{ V}$, $I_c=75\text{ A}$, $V_{GE}=\pm 15\text{ V}$, INDUCTIVE LOAD
 —: $T_{vj}=150\text{ }^\circ\text{C}$, - - - -: $T_{vj}=125\text{ }^\circ\text{C}$



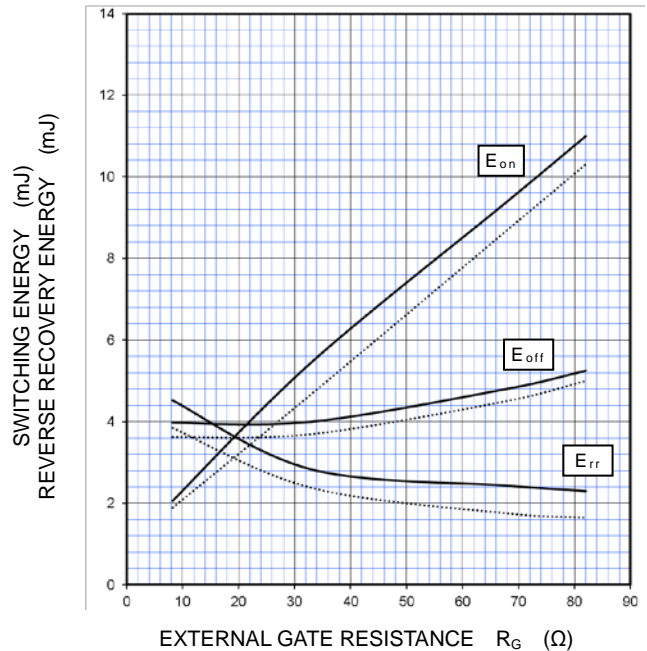
HALF-BRIDGE SWITCHING CHARACTERISTICS (TYPICAL)

$V_{CC}=300\text{ V}$, $R_G=8.2\ \Omega$, $V_{GE}=\pm 15\text{ V}$, INDUCTIVE LOAD,
 —: $T_{vj}=150\text{ }^\circ\text{C}$, - - - -: $T_{vj}=125\text{ }^\circ\text{C}$, PER PULSE



HALF-BRIDGE SWITCHING CHARACTERISTICS (TYPICAL)

$V_{CC}=300\text{ V}$, $I_c/I_E=75\text{ A}$, $V_{GE}=\pm 15\text{ V}$, INDUCTIVE LOAD,
 —: $T_{vj}=150\text{ }^\circ\text{C}$, - - - -: $T_{vj}=125\text{ }^\circ\text{C}$, PER PULSE



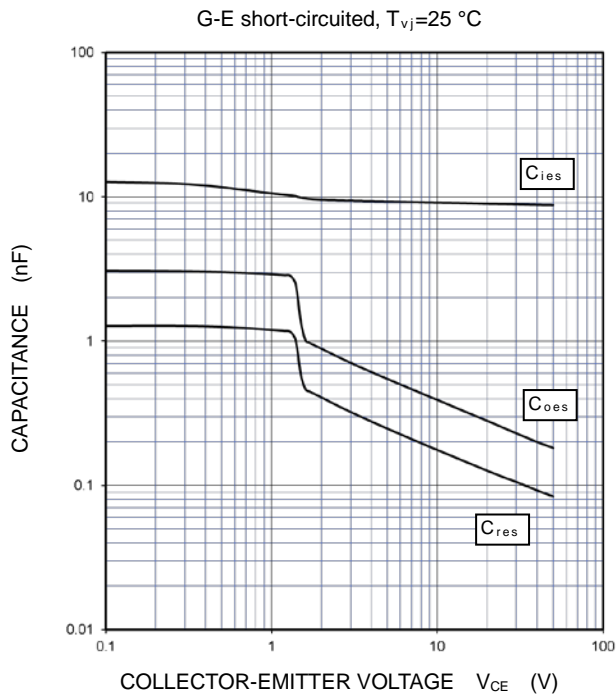
CM75MXUB-13T/CM75MXUBP-13T

HIGH POWER SWITCHING USE
INSULATED TYPE

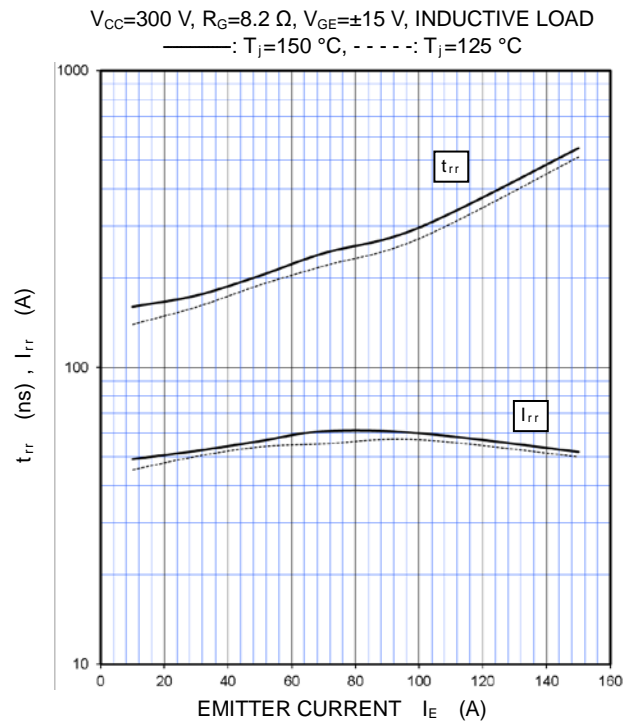
PERFORMANCE CURVES

INVERTER PART

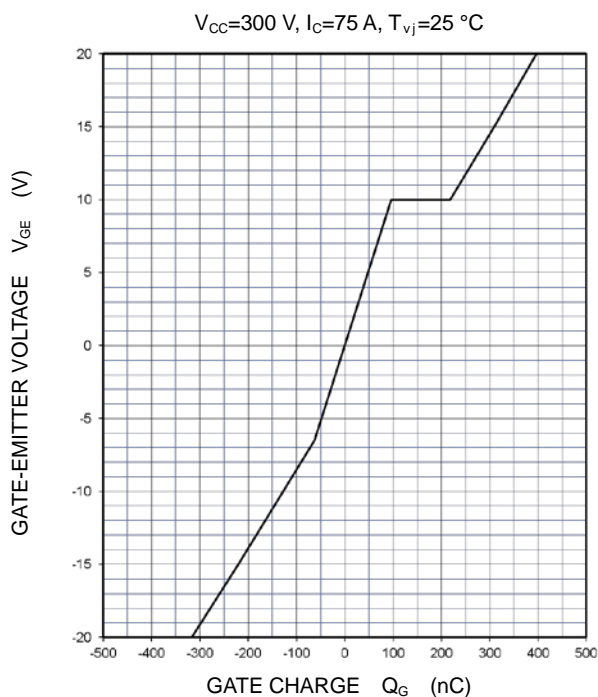
CAPACITANCE CHARACTERISTICS (TYPICAL)



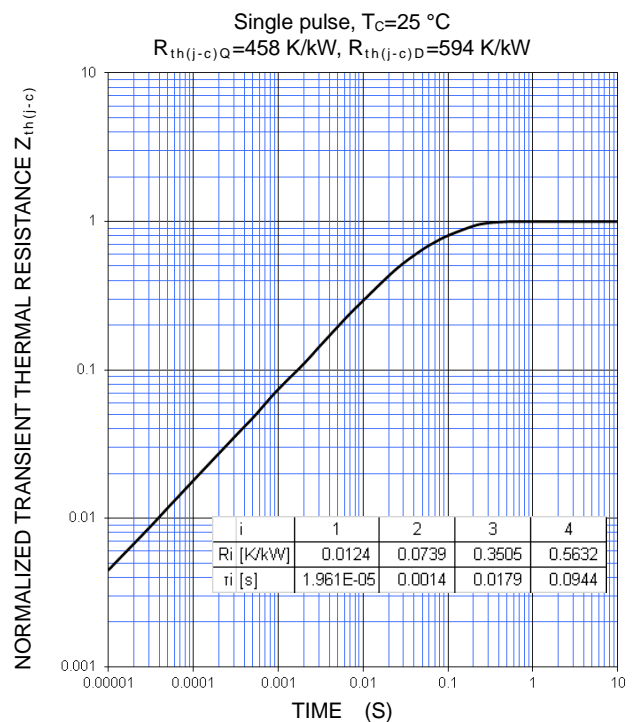
FREE WHEELING DIODE REVERSE RECOVERY CHARACTERISTICS (TYPICAL)



GATE CHARGE CHARACTERISTICS (TYPICAL)



TRANSIENT THERMAL IMPEDANCE CHARACTERISTICS (MAXIMUM)



CM75MXUB-13T/CM75MXUBP-13T

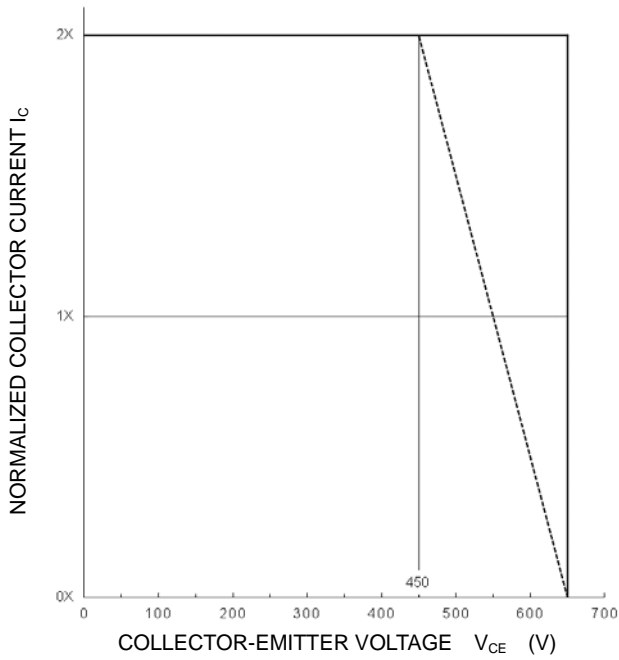
HIGH POWER SWITCHING USE
INSULATED TYPE

PERFORMANCE CURVES

INVERTER PART

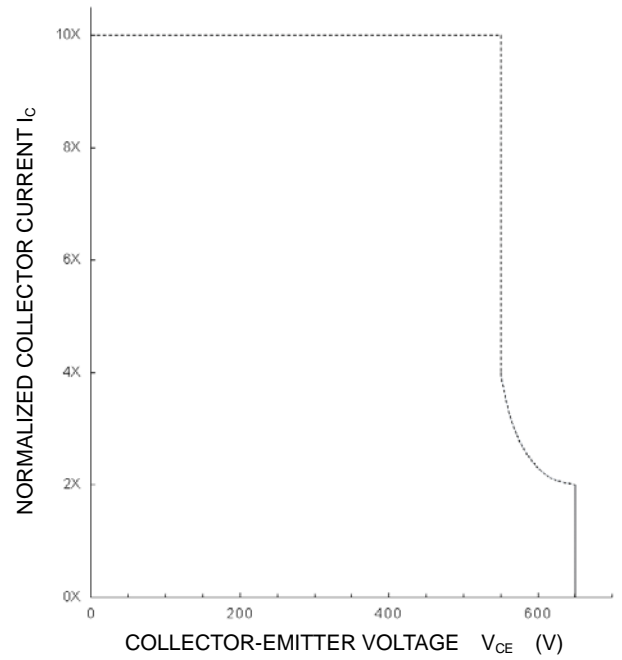
**TURN-OFF SWITCHING SAFE OPERATING AREA
(REVERSE BIAS SAFE OPERATING AREA)
(MAXIMUM)**

$V_{CC} \leq 450 \text{ V}$, $R_G = 8.2 \sim 82 \ \Omega$, $V_{GE} = \pm 15 \text{ V}$,
——: $T_{vj} = 25 \sim 150 \text{ }^\circ\text{C}$ (Normal load operations (Continuous))
- - - - -: $T_{vj} = 175 \text{ }^\circ\text{C}$ (Unusual load operations (Limited period))



**SHORT-CIRCUIT SAFE OPERATING AREA
(MAXIMUM)**

$V_{CC} \leq 400 \text{ V}$, $R_G = 8.2 \sim 82 \ \Omega$, $V_{GE} = \pm 15 \text{ V}$,
 $T_{vj} = 25 \sim 150 \text{ }^\circ\text{C}$, $t_W \leq 8 \ \mu\text{s}$, Non-Repetitive



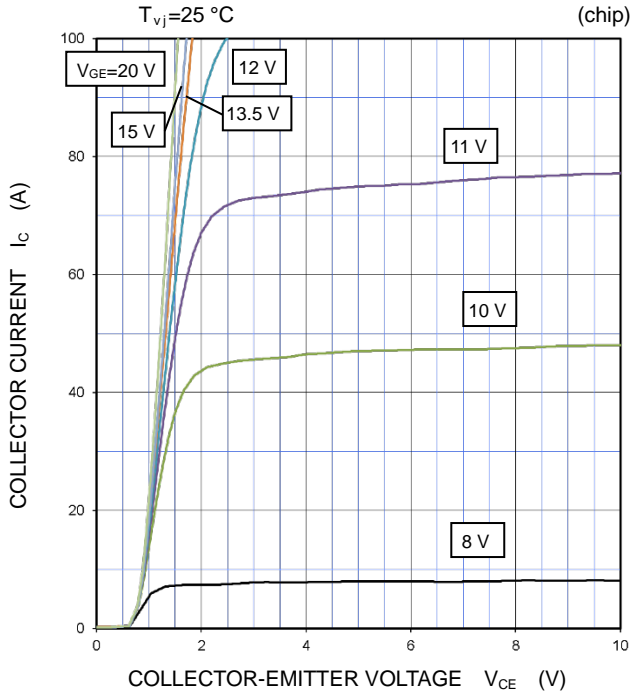
CM75MXUB-13T/CM75MXUBP-13T

HIGH POWER SWITCHING USE
INSULATED TYPE

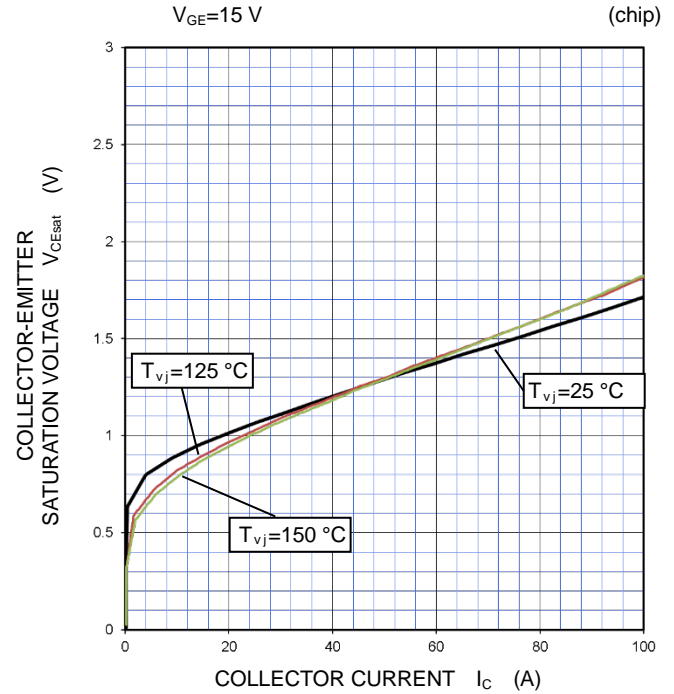
PERFORMANCE CURVES

BRAKE PART

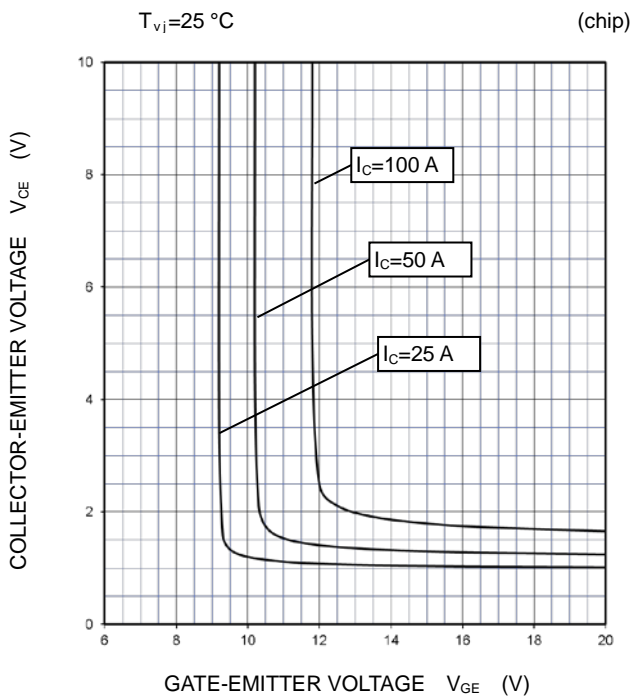
OUTPUT CHARACTERISTICS (TYPICAL)



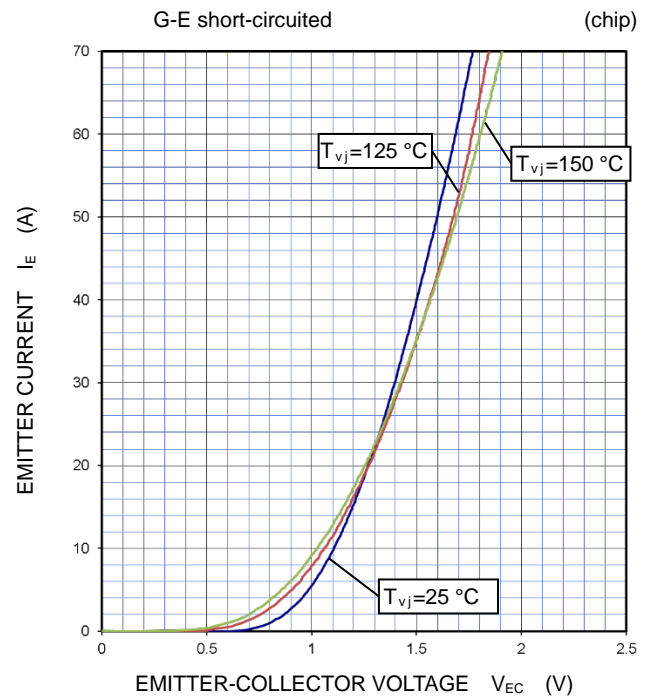
COLLECTOR-EMITTER SATURATION VOLTAGE CHARACTERISTICS (TYPICAL)



COLLECTOR-EMITTER VOLTAGE CHARACTERISTICS (TYPICAL)



DIODE FORWARD CHARACTERISTICS (TYPICAL)



CM75MXUB-13T/CM75MXUBP-13T

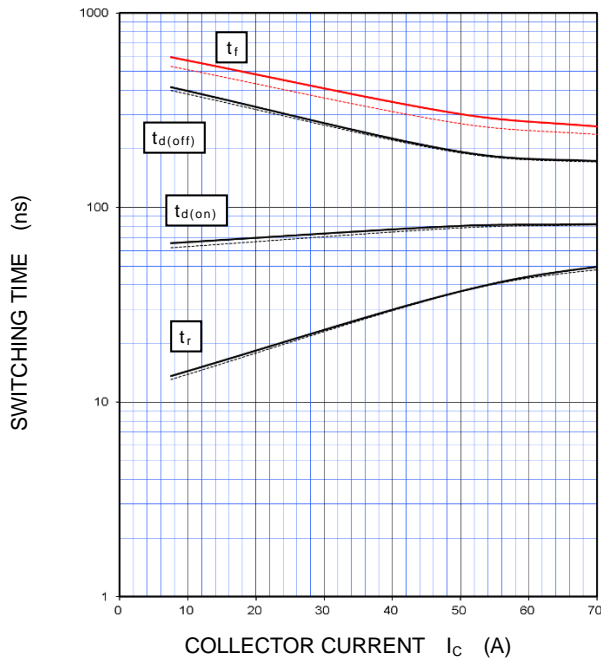
HIGH POWER SWITCHING USE
INSULATED TYPE

PERFORMANCE CURVES

BRAKE PART

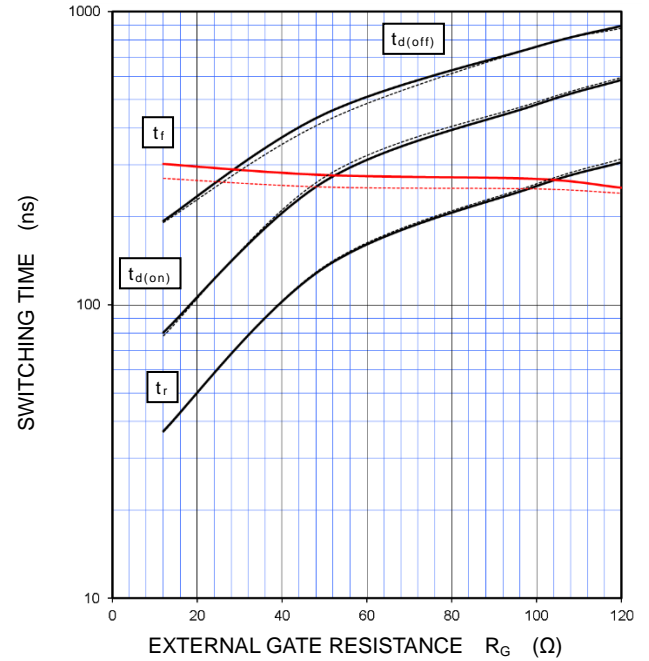
HALF-BRIDGE SWITCHING CHARACTERISTICS (TYPICAL)

$V_{CC}=300\text{ V}$, $R_G=12\ \Omega$, $V_{GE}=\pm 15\text{ V}$, INDUCTIVE LOAD
 —: $T_{vj}=150\text{ }^\circ\text{C}$, - - - -: $T_{vj}=125\text{ }^\circ\text{C}$



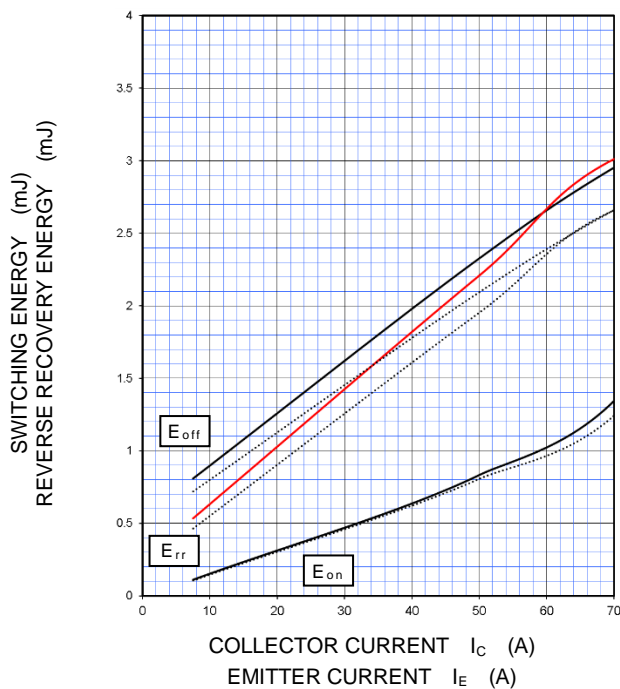
HALF-BRIDGE SWITCHING CHARACTERISTICS (TYPICAL)

$V_{CC}=300\text{ V}$, $I_c=50\text{ A}$, $V_{GE}=\pm 15\text{ V}$, INDUCTIVE LOAD
 —: $T_{vj}=150\text{ }^\circ\text{C}$, - - - -: $T_{vj}=125\text{ }^\circ\text{C}$



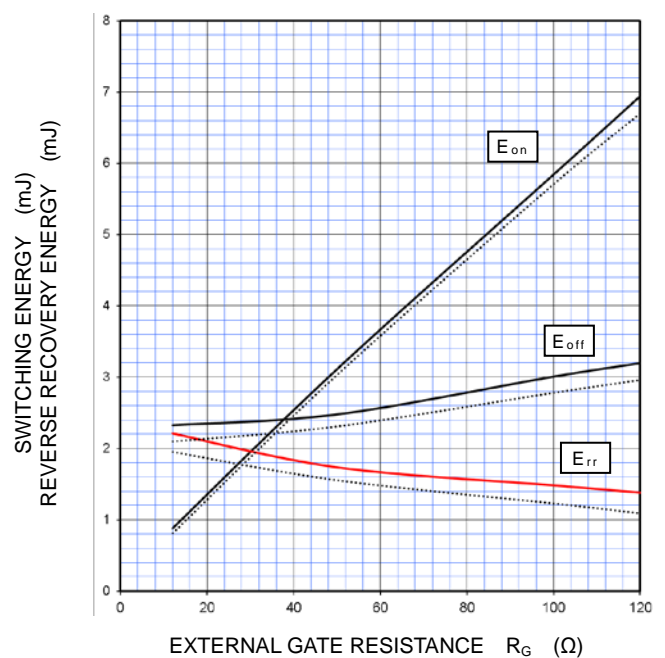
HALF-BRIDGE SWITCHING CHARACTERISTICS (TYPICAL)

$V_{CC}=300\text{ V}$, $R_G=12\ \Omega$, $V_{GE}=\pm 15\text{ V}$, INDUCTIVE LOAD,
 —: $T_{vj}=150\text{ }^\circ\text{C}$, - - - -: $T_{vj}=125\text{ }^\circ\text{C}$, PER PULSE



HALF-BRIDGE SWITCHING CHARACTERISTICS (TYPICAL)

$V_{CC}=300\text{ V}$, $I_c/I_E=50\text{ A}$, $V_{GE}=\pm 15\text{ V}$, INDUCTIVE LOAD,
 —: $T_{vj}=150\text{ }^\circ\text{C}$, - - - -: $T_{vj}=125\text{ }^\circ\text{C}$, PER PULSE



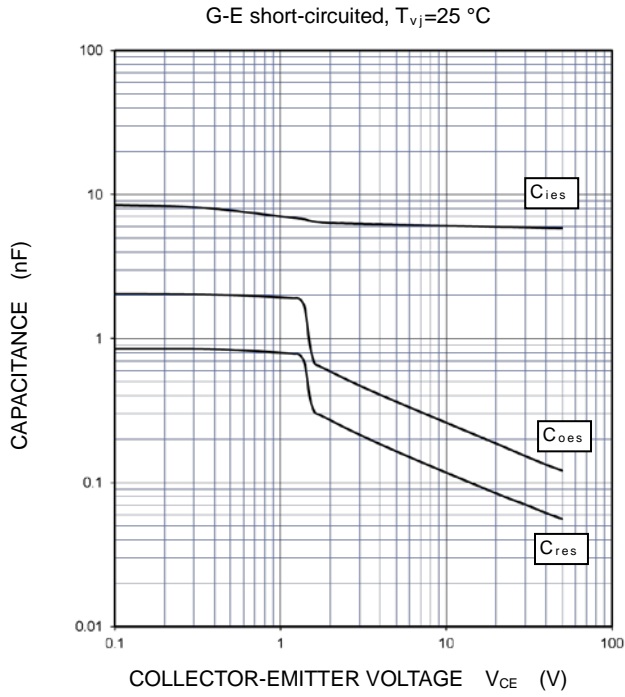
CM75MXUB-13T/CM75MXUBP-13T

HIGH POWER SWITCHING USE
INSULATED TYPE

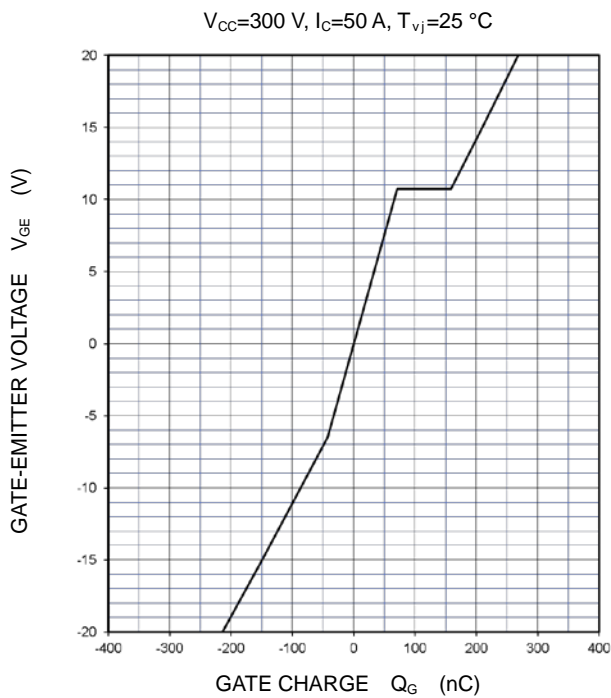
PERFORMANCE CURVES

BRAKE PART

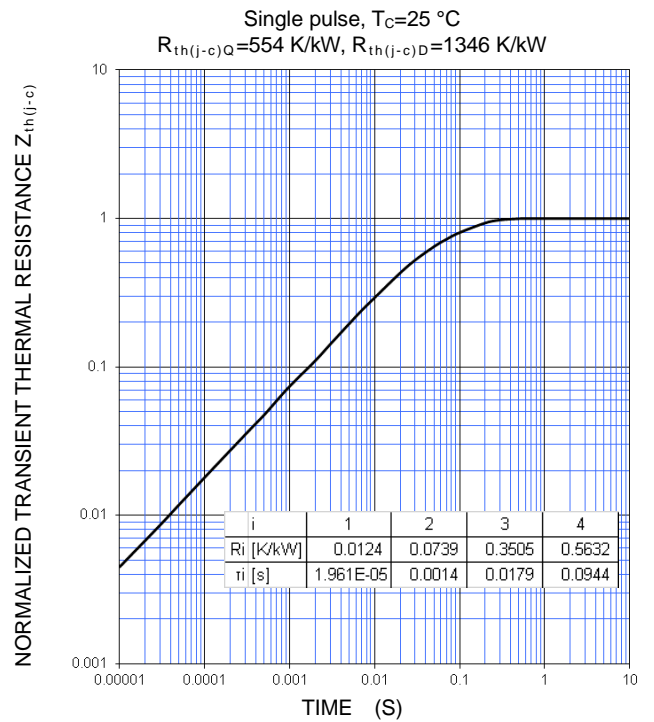
CAPACITANCE CHARACTERISTICS (TYPICAL)



GATE CHARGE CHARACTERISTICS (TYPICAL)



TRANSIENT THERMAL IMPEDANCE CHARACTERISTICS (MAXIMUM)



CM75MXUB-13T/CM75MXUBP-13T

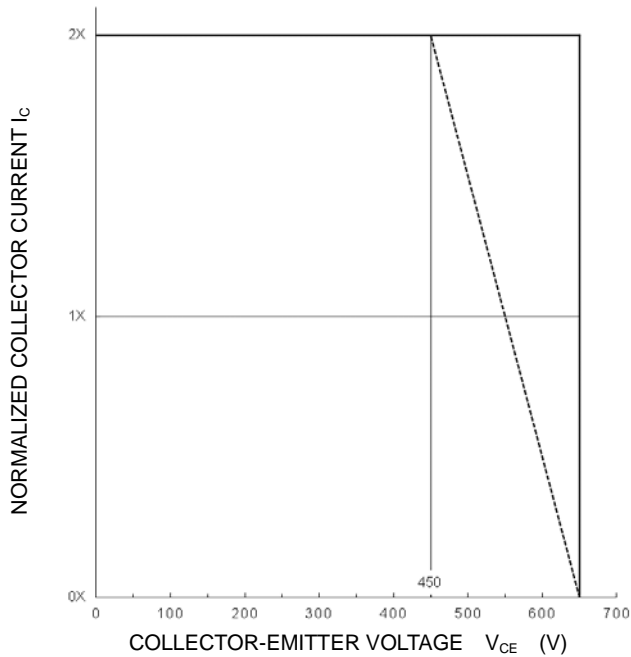
HIGH POWER SWITCHING USE
INSULATED TYPE

PERFORMANCE CURVES

BRAKE PART

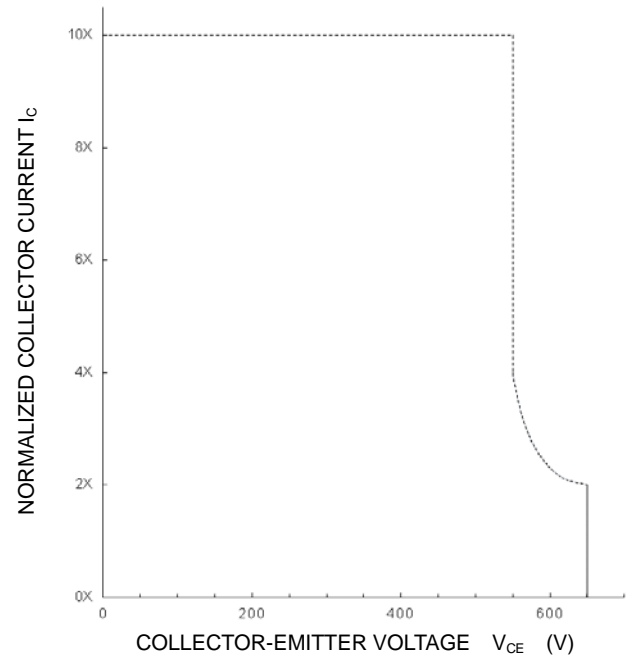
**TURN-OFF SWITCHING SAFE OPERATING AREA
(REVERSE BIAS SAFE OPERATING AREA)
(MAXIMUM)**

$V_{CC} \leq 450 \text{ V}$, $R_G = 12 \sim 120 \ \Omega$, $V_{GE} = \pm 15 \text{ V}$,
 ———: $T_{vj} = 25 \sim 150 \text{ }^\circ\text{C}$ (Normal load operations (Continuous))
 - - - - -: $T_{vj} = 175 \text{ }^\circ\text{C}$ (Unusual load operations (Limited period))



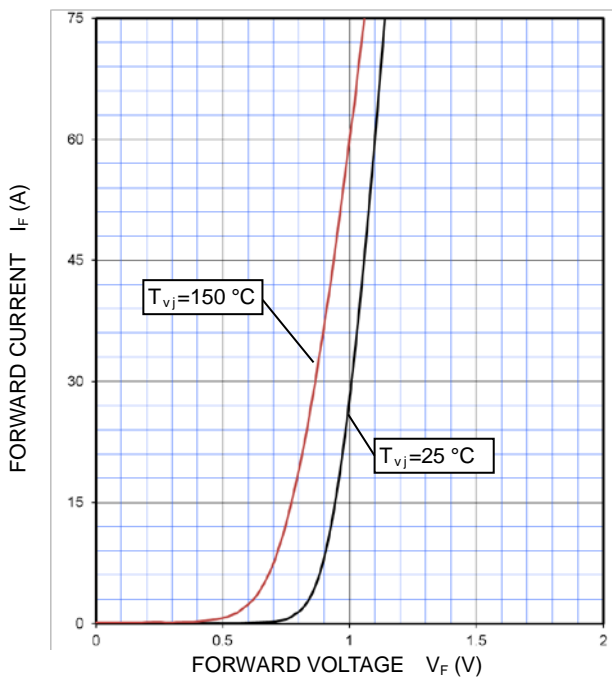
**SHORT-CIRCUIT SAFE OPERATING AREA
(MAXIMUM)**

$V_{CC} \leq 400 \text{ V}$, $R_G = 12 \sim 120 \ \Omega$, $V_{GE} = \pm 15 \text{ V}$,
 $T_{vj} = 25 \sim 150 \text{ }^\circ\text{C}$, $t_W \leq 8 \ \mu\text{s}$, Non-Repetitive



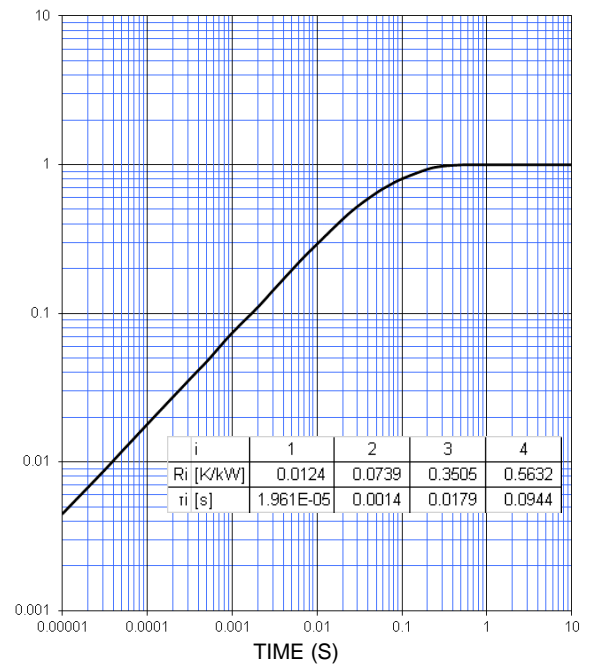
CONVERTER PART

**CONVERTER DIODE
FORWARD CHARACTERISTICS
(TYPICAL)**



**TRANSIENT THERMAL IMPEDANCE CHARACTERISTICS
(MAXIMUM)**

Single pulse, $T_C = 25 \text{ }^\circ\text{C}$
 $R_{th(j-c)D} = 650 \text{ K/kW}$



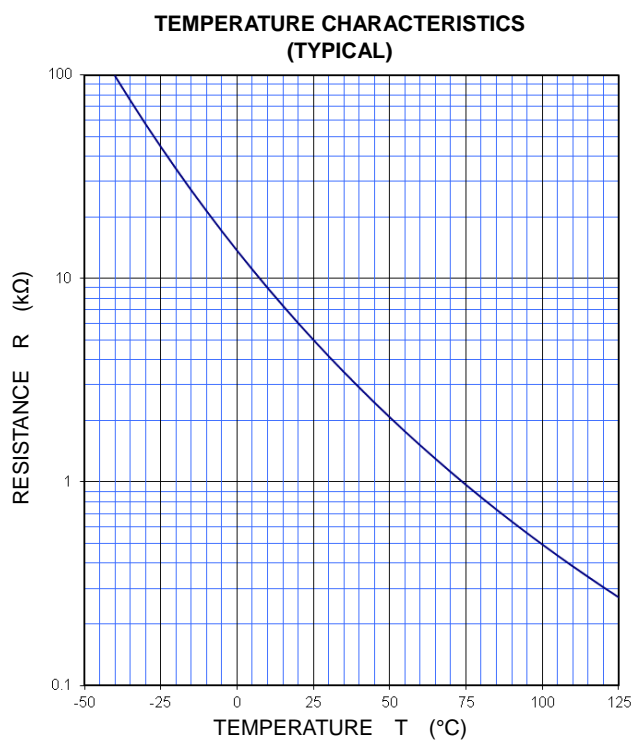
CM75MXUB-13T/CM75MXUBP-13T

HIGH POWER SWITCHING USE

INSULATED TYPE

PERFORMANCE CURVES

NTC thermistor part



Note: The characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.

Keep safety first in your circuit designs!

This product is designed for industrial application purpose. The performance, the quality and support level of the product is guaranteed by "Customer's Std. Spec."

Mitsubishi Electric Corporation puts its reasonable effort into making semiconductor products better and more reliable, but there is always the possibility that trouble may occur with them by the reliability lifetime such as Power Cycle, Thermal Cycle or others, or to be used under special circumstances (e.g. high humidity, dusty, salty, highlands, environment with lots of organic matter / corrosive gas / explosive gas, or situation which terminal of semiconductor products is received strong mechanical stress).

In the customer's research and development, please evaluate it not only with a single semiconductor product but also in the entire system, and judge whether it's applicable. Furthermore, trouble with semiconductors may lead to personal injury, fire or property damage. Remember to give due consideration to safety when making your circuit designs, with appropriate measures such as (i) placement of substitutive, auxiliary circuits (e.g. appropriate fuse or circuit breaker between a power supply and semiconductor products), (ii) use of non-flammable material or (iii) prevention against any malfunction or mishap.

Notes regarding these materials

- These materials are intended as a reference to assist our customers in the selection of the Mitsubishi semiconductor product best suited to the customer's application; they do not convey any license under any intellectual property rights, or any other rights, belonging to Mitsubishi Electric Corporation or a third party.
- Mitsubishi Electric Corporation assumes no responsibility for any damage, or infringement of any third-party's rights, originating in the use of any product data, diagrams, charts, or circuit application examples contained in these materials.

- All information contained in these materials, including product data, diagrams and charts represents information on products at the time of publication of these materials, and are subject to change by Mitsubishi Electric Corporation without notice due to product improvements or other reasons. It is therefore recommended that customers contact Mitsubishi Electric Corporation or an authorized Mitsubishi Semiconductor product distributor for the latest product information before purchasing a product listed herein.

The information described here may contain technical inaccuracies or typographical errors. Mitsubishi Electric Corporation assumes no responsibility for any damage, liability, or other loss rising from these inaccuracies or errors.

Please also pay attention to information published by Mitsubishi Electric Corporation by various means, including the Mitsubishi Semiconductor home page (www.MitsubishiElectric.com/semiconductors/).

- When using any or all of the information contained in these materials, including product data, diagrams, and charts, please be sure to evaluate all information as a total system before making a final decision on the applicability of the information and products. Mitsubishi Electric Corporation assumes no responsibility for any damage, liability or other loss resulting from the information contained herein.

- Mitsubishi Electric Corporation semiconductors are not designed or manufactured for use in a device or system that is used under circumstances in which human life is potentially at stake. Therefore, this product should not be used in such applications.

Please contact Mitsubishi Electric Corporation or an authorized Mitsubishi Semiconductor product distributor when considering the use of a product contained herein for any specific purposes, such as apparatus or systems for transportation, vehicular, medical, aerospace, nuclear, or undersea repeater use.

- In the case of new requirement is available, this material will be revised upon consultation.
- The prior written approval of Mitsubishi Electric Corporation is necessary to reprint or reproduce in whole or in part these materials.
- If these products or technologies are subject to the Japanese export control restrictions, they must be exported under a license from the Japanese government and cannot be imported into a country other than the approved destination. Any diversion or re-export contrary to the export control laws and regulations of Japan and/or the country of destination is prohibited.
- Please contact Mitsubishi Electric Corporation or an authorized Mitsubishi Semiconductor product distributor for further details on these materials or the products contained therein.

The company names and the product names described herein are the trademarks or registered trademarks of the respective companies.